



IN THE SPECIFICATION

Please replace the second paragraph on page 11, with the following:

Once the high quality base of the crystal has accumulated enough mass, the growth rate can be increased to increase vertical growth on the crystal base. In this step, the pressure is lowered from  $P_1$  to  $P_2$  ~~in~~ for about 3-8 hours for bulk vertical crystal growth (see Fig. 5). The pressure should be low enough to permit SiC vapor species to reach the growing crystal surface and provide a growth rate of about 0.1 to 2.0 mm/hr for at least 3 hours. The growth rate is preferably set at less than 1.0 mm/hr for a duration of 5 hours. Again, the temperatures  $T_{\text{seed}}$  and  $T_{\text{source}}$  remain the same throughout the entire growth process until a SiC single crystal 24 is fully grown as shown in Fig. 4 (the amount of sublimation of the source material is represented by depth 26).